

**AMENDMENTS TO THE SPECIFICATION**

Please replace the paragraph beginning on page 4, line 28 with the following amended paragraph:

That is, the CMP slurry composition for oxide film of the present invention includes the  $\text{HXO}_n$  compound, and thus the polishing selectivity ratio of for a nitride hard mask film to an interlayer insulating film formed of an oxide film ~~to a nitride hard mask film~~ is ranges from 1:1 to 1:3, preferably from 1:1 to 1:2, ~~and the polishing selectivity ratio of the oxide film to the silicon layer is 1:3, preferably 1:2.~~

Please replace the paragraph beginning on page 6, line 7 with the following amended paragraph:

A word line pattern 114 having a hard mask pattern 113 on a conductive layer pattern ~~2~~ 112 for word line is formed by sequentially etching the hard mask film and the conductive layer for word line.

Please replace the paragraph beginning on page 6, line 29 with the following amended paragraph:

The etching process is performed by a self-aligned contact (SAC) process using  $\text{C}_4\text{F}_8$ ,  $\text{C}_2\text{F}_6$  or  $\text{C}_3\text{F}_8$  source having a high ~~polishing~~ etching selectivity ratio to the nitride film, preferably  $\text{C}_4\text{F}_8$  source.